SM7340EHKP

Dual N-Channel Enhancement Mode MOSFET

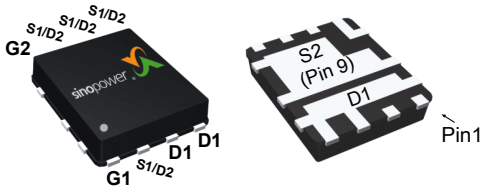
Features

- **Channel 1**
  30V/31A,
  $R_{DS(ON)}$ = 2.5mΩ (max.) @ V_{GS} = 10V
  $R_{DS(ON)}$ = 4.2mΩ (max.) @ V_{GS} = 4.5V
- **Channel 2**
  30V/56A,
  $R_{DS(ON)}$ = 0.75mΩ (max.) @ V_{GS} =10V
  $R_{DS(ON)}$ = 1.2mΩ (max.) @ V_{GS} =4.5V
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free Available (RoHS Compliant)
- Dual Dies Package and Minimize Board Space
- Lower Q_g and Q_{gd} for High-Speed Switching
- Lower $R_{DS(ON)}$ to Minimize Conduction Losses

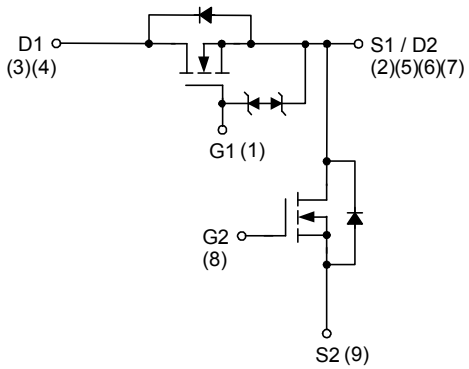
Applications

- Power Management in Desktop Computer or DC/DC Converters.

Pin Description



DFN5x6E-8_EP2



N-Channel MOSFET

Ordering and Marking Information

SM7340EH □□□-□□ □ Assembly Material Handling Code Temperature Range Package Code	Package Code KP : DFN5x6E-8_EP2 Operating Junction Temperature Range C : -55 to 150 °C Handling Code TR : Tape & Reel Assembly Material G : Halogen and Lead Free Device
SM7340EH KP : 7340EH XXXXX	XXXXX - Lot Code

Note : SINOPOWER lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. SINOPOWER lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. SINOPOWER defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

Symbol	Parameter		Channel 1	Channel 2	Unit
Common Ratings					
V_{DSS}	Drain-Source Voltage		30		V
V_{GSS}	Gate-Source Voltage		±20		V
T_J	Maximum Junction Temperature		150		°C
T_{STG}	Storage Temperature Range		-55 to 150		°C
I_S	Diode Continuous Forward Current	T_C=25°C	20	40	A
I_D	Continuous Drain Current	T_C=25°C	102	292	A
		T_C=100°C	40	185	
I_{DM} [a]	Pulse Drain Current	T_C=25°C	200	350	A
P_D	Maximum Power Dissipation	T_C=25°C	39	96	W
		T_C=100°C	15.6	38.4	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	Steady State	3.2	1.3	°C/W
I_D [b]	Continuous Drain Current	T_A=25°C	31	56	A
		T_A=70°C	25	45	
I_{DM}	Pulse Drain Current(T=300uS)	T_A=25°C	80	140	A
P_D [b]	Maximum Power Dissipation	T_A=25°C	3.6	3.6	W
		T_A=70°C	2.3	2.3	
$R_{\theta JA}$ [b,c]	Thermal Resistance-Junction to Ambient	t ≤10s	35	35	°C/W
		Steady State	75	75	
$R_{\theta JA}$ [d]	Thermal Resistance-Junction to Ambient	Steady State	120	120	°C/W
I_{AS} [e]	Avalanche Current, Single pulse	L=0.1mH	35	65	A
E_{AS} [e]	Avalanche Energy, Single pulse	L=0.1mH	61.25	211.25	mJ

Note a：Pulse width is limited by max. junction temperature.
Note b：t ≤10s and surface mounted on FR-4 board using 1in^2 pad, 2 oz Cu.
Note c：Steady time = 999s and surface mounted on FR-4 board using 1in^2 pad, 2 oz Cu.
Note d：Steady time = 999s and surface mounted on FR-4 board and the minimum pad size of PCB.
Note e：UIS tested and pulse width are limited by maximum junction temperature 150°C(initial temperature T_j=25°C).

Channel 1 Electrical Characteristics (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Channel 1			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250μA	30	-	-	V
BV_{DSSt}	Drain-Source Breakdown Voltage (transient)	V_{GS}=0V, $I_{D(aval)}$=35A T_{case}=25°C, $t_{transient}$=100ns	34	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=24V, V_{GS}=0V	-	-	1	μA
		T_J=85°C	-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250μA	1.3	1.6	2.3	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V	-	-	±10	μA
$R_{DS(ON)}$ [f]	Drain-Source On-state Resistance	V_{GS}=10V, I_{DS}=15A	-	2	2.5	mΩ
		T_J=125°C	-	3	-	
		V_{GS}=4.5V, I_{DS}=12A	-	3.2	4.2	
Gfs	Forward Transconductance	V_{DS}=5V, I_{DS}=15A	-	20	-	S
Diode Characteristics						
V_{SD} [f]	Diode Forward Voltage	I_{SD}=15A, V_{GS}=0V	-	0.78	1.1	V
t_{rr}	Reverse Recovery Time	I_{SD}=15A, dI_{SD}/dt=100A/μs V_{dd}=15V	-	32.4	-	ns
t_a	Charge Time		-	16	-	
t_b	Discharge Time		-	16.4	-	
Q_{rr}	Reverse Recovery Charge		-	19	-	nC
Dynamic Characteristics [g]						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V,F=1MHz	-	1.2	-	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, Frequency=1.0MHz	-	1670	-	pF
C_{oss}	Output Capacitance		-	1140	-	
C_{rss}	Reverse Transfer Capacitance		-	83	-	
$t_{d(ON)}$	Turn-on Delay Time	V_{DD}=15V, R_L=15Ω, I_{DS}=1A, V_{GEN}=10V, R_G=1Ω	-	15	-	ns
t_r	Turn-on Rise Time		-	12	-	
$t_{d(OFF)}$	Turn-off Delay Time		-	31	-	
t_f	Turn-off Fall Time		-	29	-	
Gate Charge Characteristics [g]						
Q_g	Total Gate Charge	V_{DS}=15V, V_{GS}=4.5V, I_{DS}=15A	-	12	-	nC
Q_g	Total Gate Charge	V_{DS}=15V, V_{GS}=10V, I_{DS}=15A	-	25	-	
Q_{gth}	Threshold Gate Charge		-	1.7	-	
Q_{gs}	Gate-Source Charge		-	2	-	
Q_{gd}	Gate-Drain Charge		-	5.5	-	

Note f：Pulse test ; pulse width≤300μs, duty cycle≤2%.

Note g：Guaranteed by design, not subject to production testing.

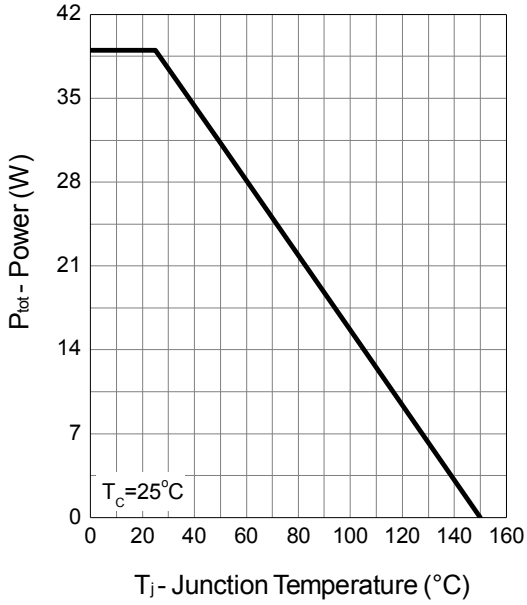
Channel 2 Electrical Characteristics (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Channel 2			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250μA	30	-	-	V
BV_{DSSt}	Drain-Source Breakdown Voltage (transient)	V_{GS}=0V, $I_{D(aval)}$=65A T_{case}=25°C, $t_{transient}$=100ns	34	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=24V, V_{GS}=0V	-	-	1	μA
		T_J=85°C	-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250μA	1.3	1.6	2.3	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
$R_{DS(ON)}$ [f]	Drain-Source On-state Resistance	V_{GS}=10V, I_{DS}=25A	-	0.6	0.75	mΩ
		T_J=125°C	-	0.91	-	
		V_{GS}=4.5V, I_{DS}=20A	-	0.9	1.2	
Gfs	Forward Transconductance	V_{DS}=5V, I_{DS}=15A	-	30	-	S
Diode Characteristics						
V_{SD} [f]	Diode Forward Voltage	I_{SD}=25A, V_{GS}=0V	-	0.76	1.1	V
t_{rr}	Reverse Recovery Time	I_{SD}=15A, dI_{SD}/dt=100A/μs V_{dd}=15V	-	69	-	ns
t_a	Charge Time		-	39	-	
t_b	Discharge Time		-	30	-	
Q_{rr}	Reverse Recovery Charge		-	83	-	nC
Dynamic Characteristics [g]						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V,F=1MHz	-	0.65	-	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, Frequency=1.0MHz	-	6600	-	pF
C_{oss}	Output Capacitance		-	3800	-	
C_{rss}	Reverse Transfer Capacitance		-	330	-	
$t_{d(ON)}$	Turn-on Delay Time	V_{DD}=15V, R_L=15Ω, I_{DS}=1A, V_{GEN}=10V, R_G=1Ω	-	25	-	ns
t_r	Turn-on Rise Time		-	19	-	
$t_{d(OFF)}$	Turn-off Delay Time		-	65	-	
t_f	Turn-off Fall Time		-	70	-	
Gate Charge Characteristics [g]						
Q_g	Total Gate Charge	V_{DS}=15V, V_{GS}=4.5V, I_{DS}=25A	-	51	-	nC
Q_g	Total Gate Charge	V_{DS}=15V, V_{GS}=10V, I_{DS}=25A	-	104	-	
Q_{gth}	Threshold Gate Charge		-	7.2	-	
Q_{gs}	Gate-Source Charge		-	14	-	
Q_{gd}	Gate-Drain Charge		-	20	-	

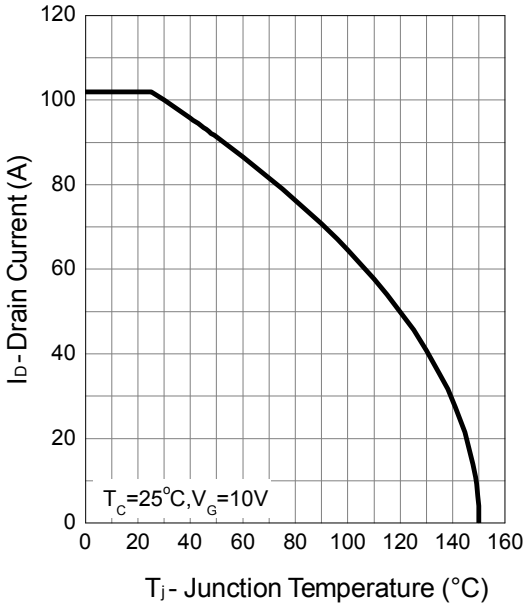
Note f : Pulse test ; pulse width≤300μs, duty cycle≤2%.
Note g : Guaranteed by design, not subject to production testing.

Channel 1 Typical Operating Characteristics

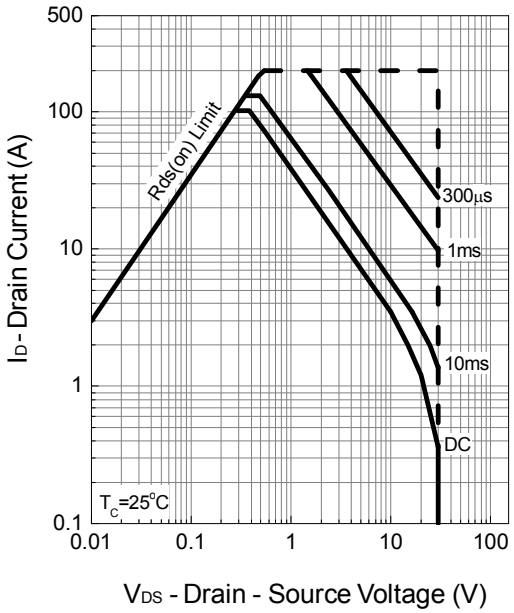
Power Dissipation



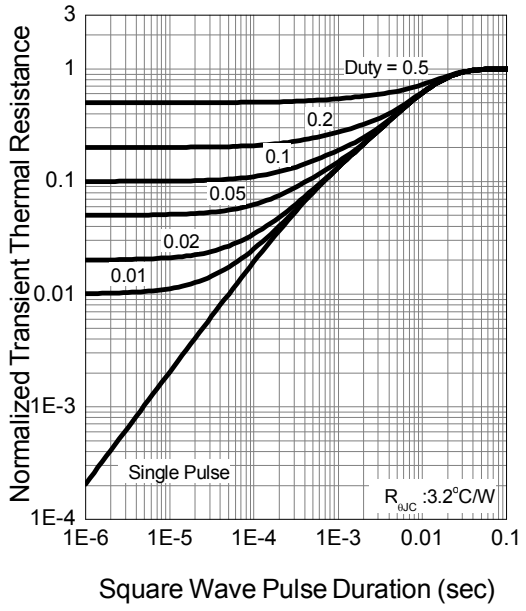
Drain Current



Safe Operation Area

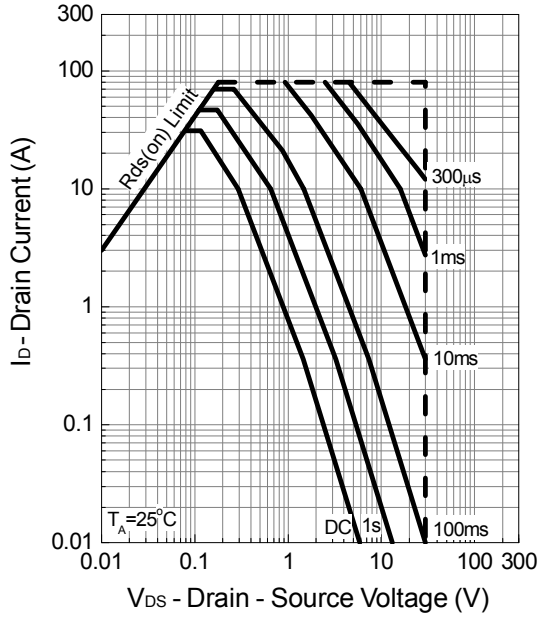


Thermal Transient Impedance

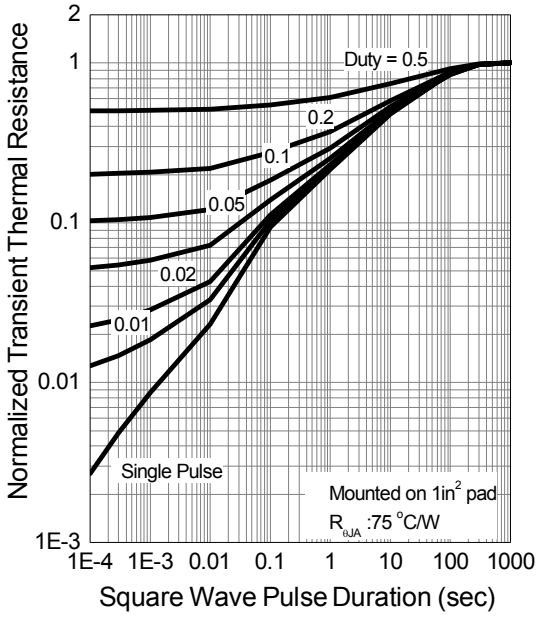


Channel 1 Typical Operating Characteristics (Cont.)

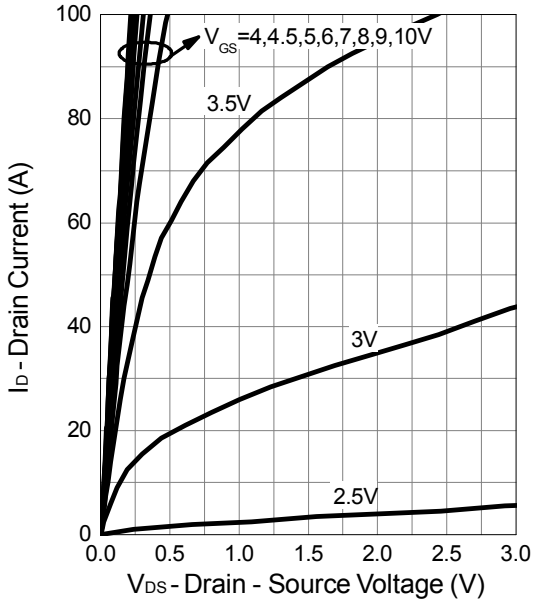
Safe Operation Area



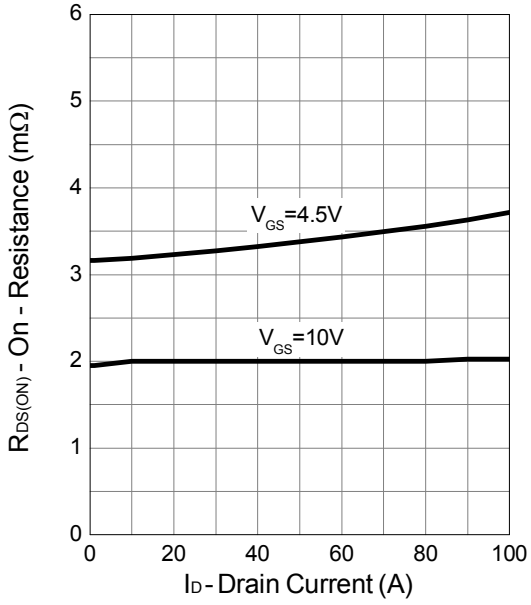
Thermal Transient Impedance



Output Characteristics

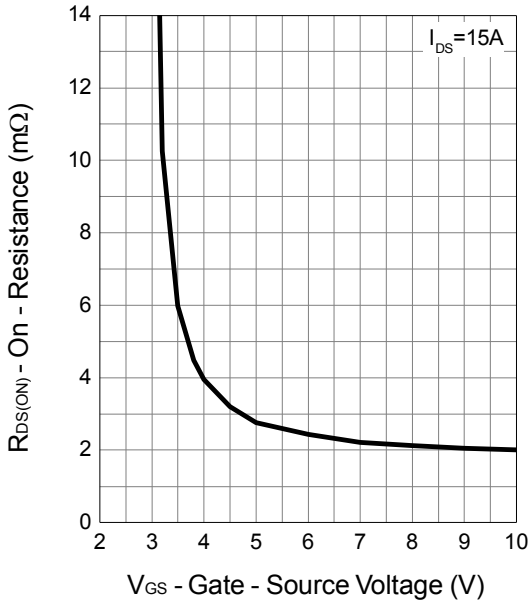


Drain-Source On Resistance

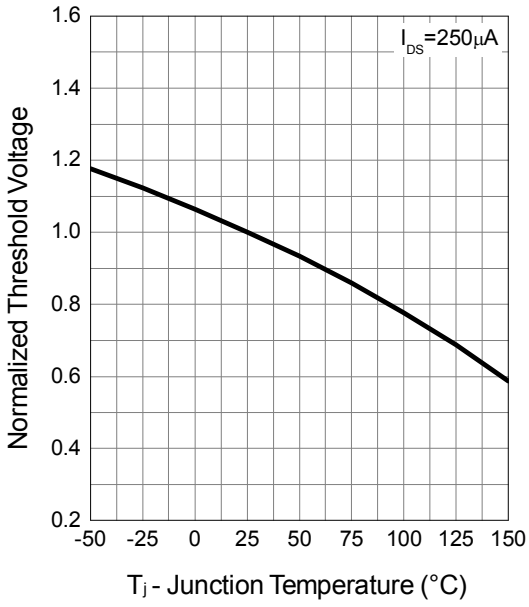


Channel 1 Typical Operating Characteristics (Cont.)

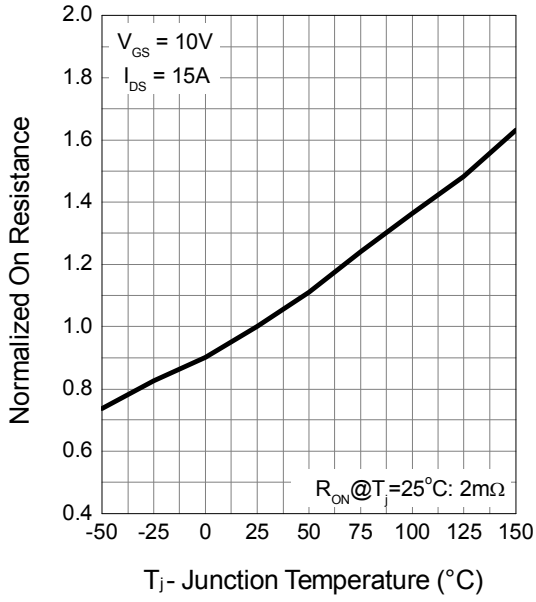
Gate-Source On Resistance



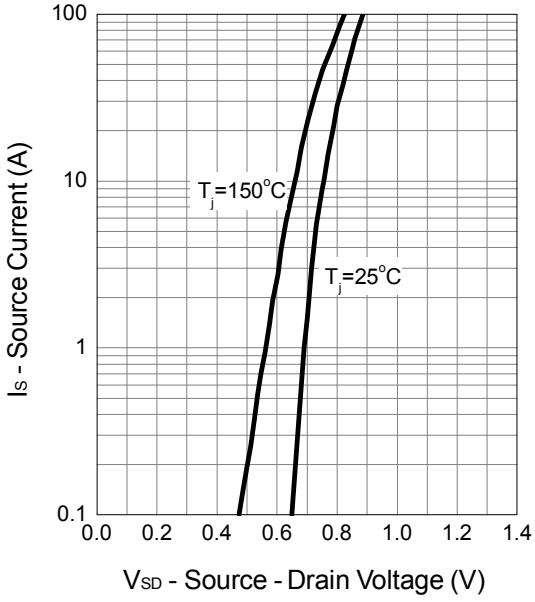
Gate Threshold Voltage



Drain-Source On Resistance

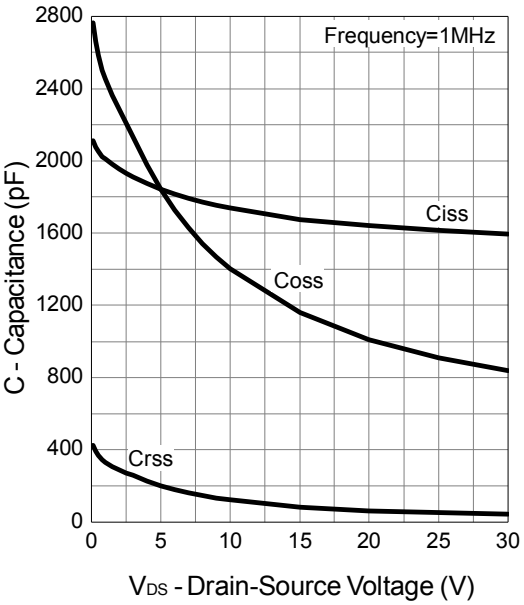


Source-Drain Diode Forward

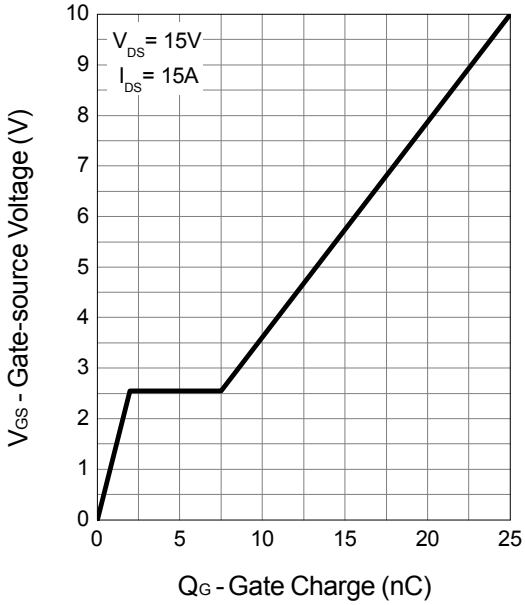


Channel 1 Typical Operating Characteristics (Cont.)

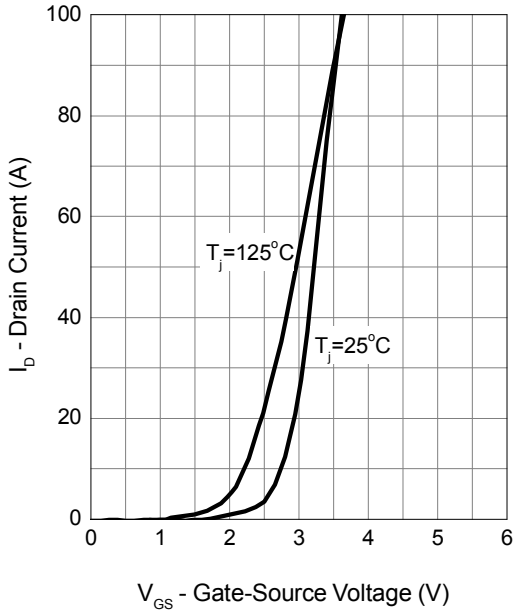
Capacitance



Gate Charge

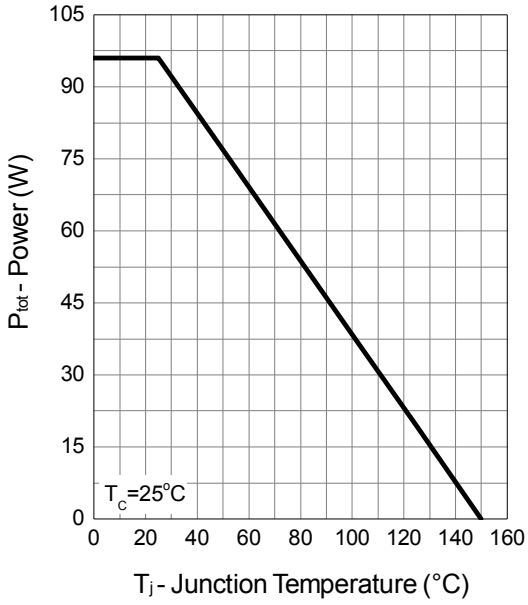


Transfer Characteristics

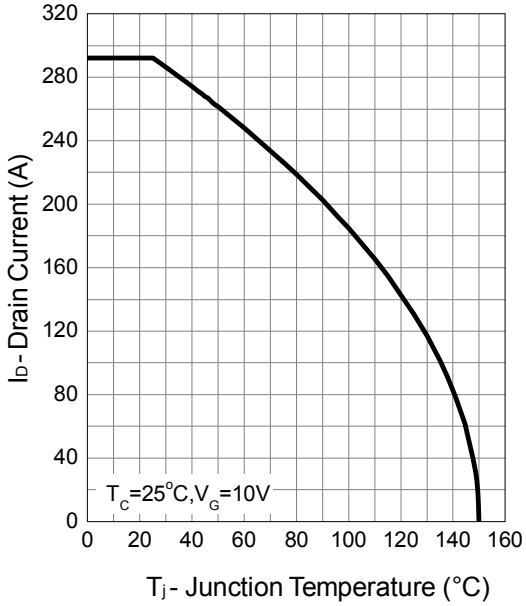


Channel 2 Typical Operating Characteristics

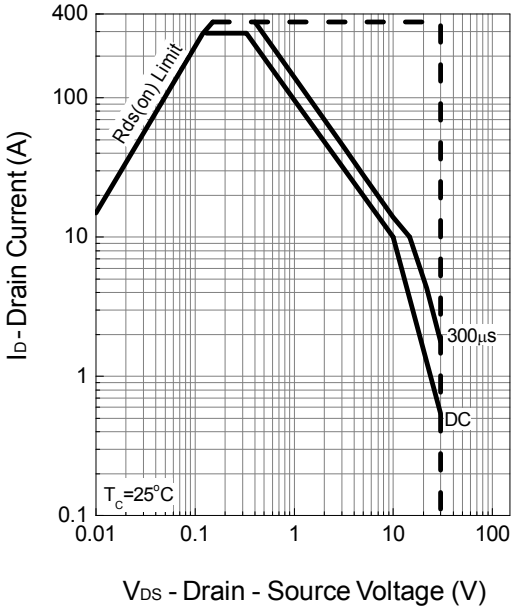
Power Dissipation



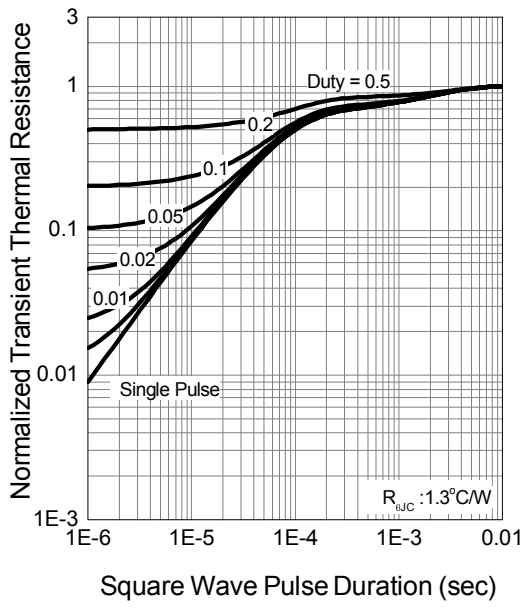
Drain Current



Safe Operation Area

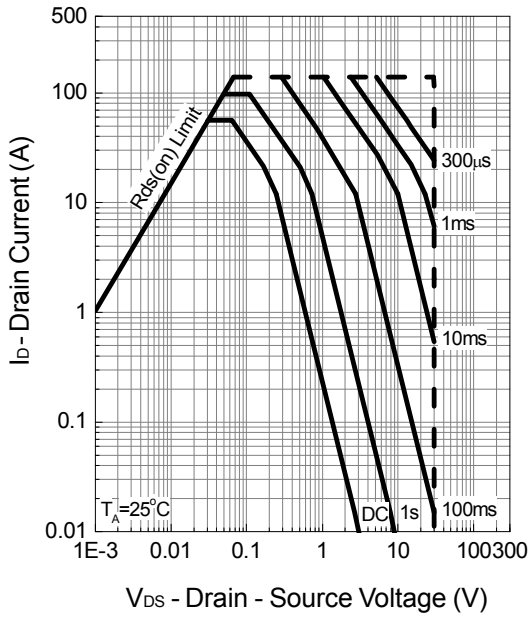


Thermal Transient Impedance

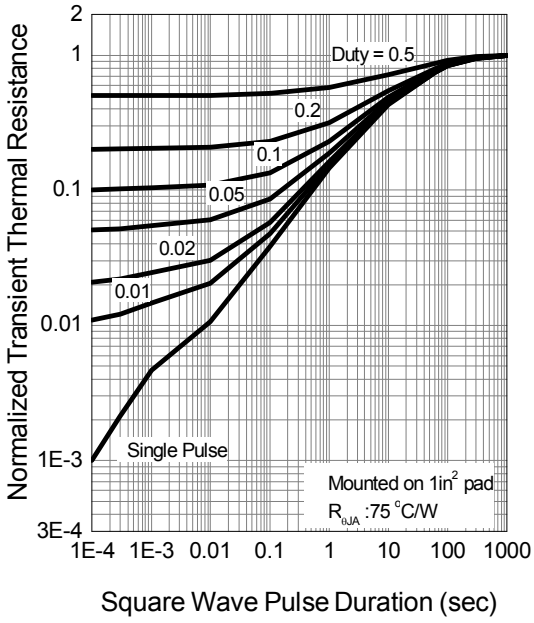


Channel 2 Typical Operating Characteristics (Cont.)

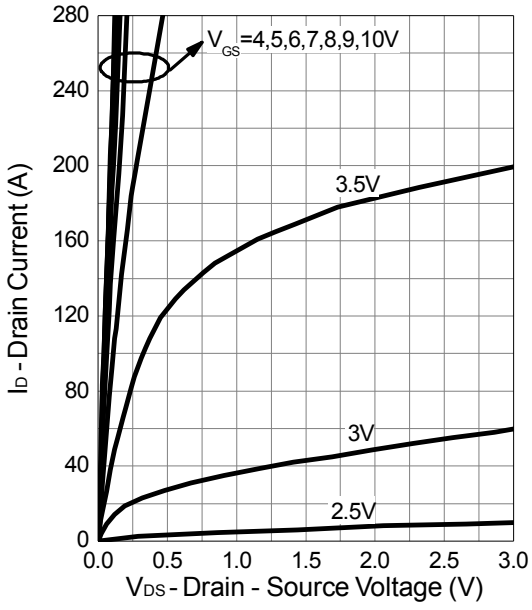
Safe Operation Area



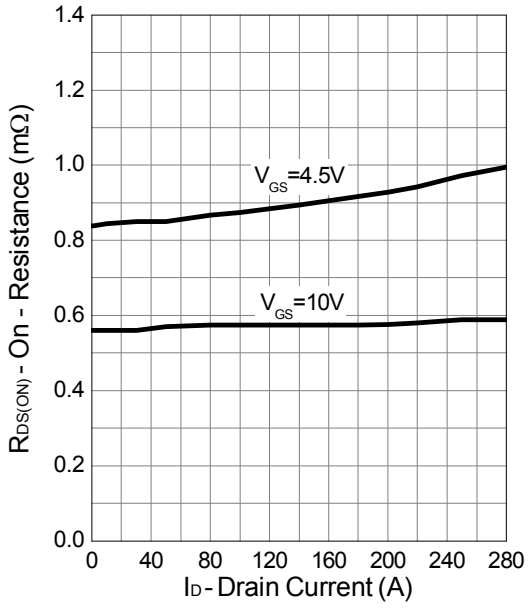
Thermal Transient Impedance



Output Characteristics

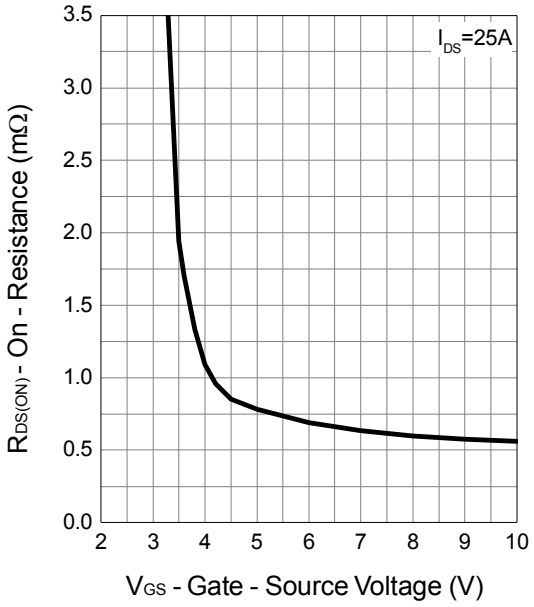


Drain-Source On Resistance

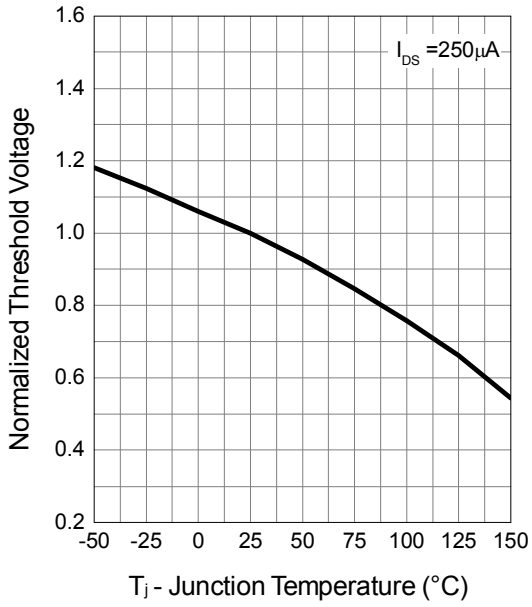


Channel 2 Typical Operating Characteristics (Cont.)

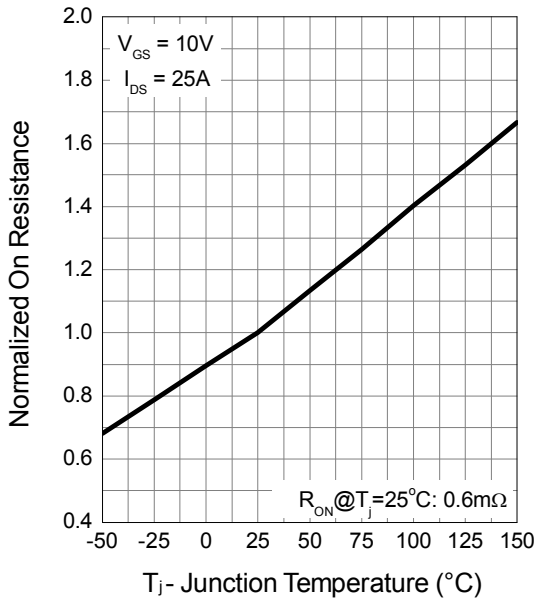
Gate-Source On Resistance



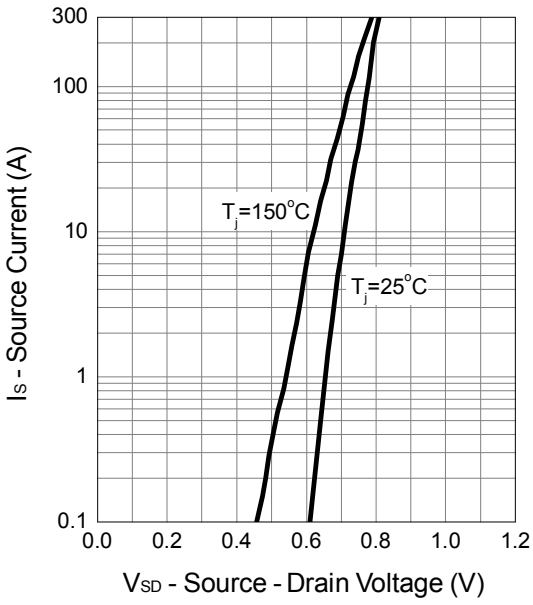
Gate Threshold Voltage



Drain-Source On Resistance

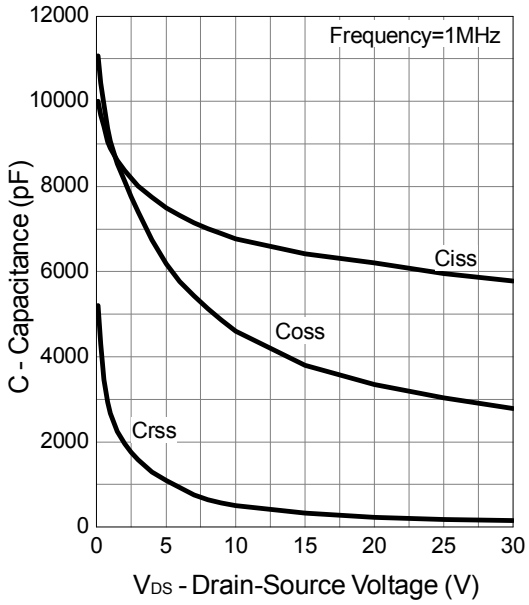


Source-Drain Diode Forward

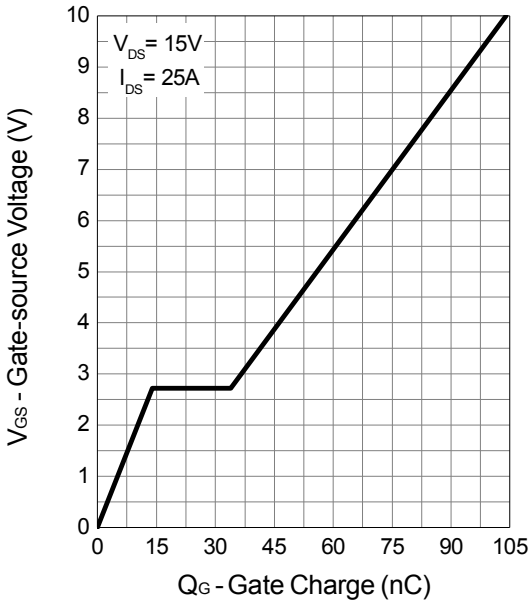


Channel 2 Typical Operating Characteristics (Cont.)

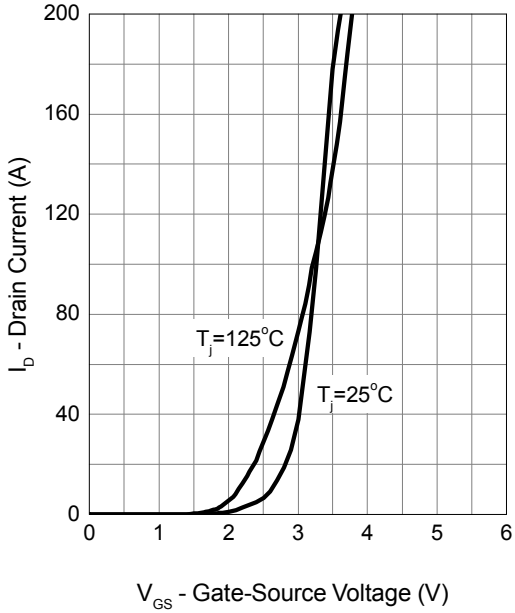
Capacitance



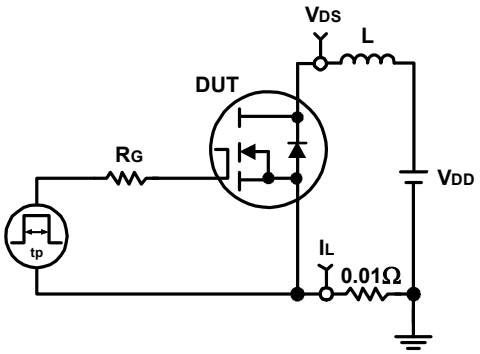
Gate Charge

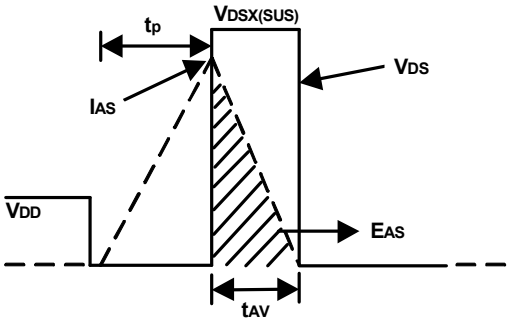


Transfer Characteristics

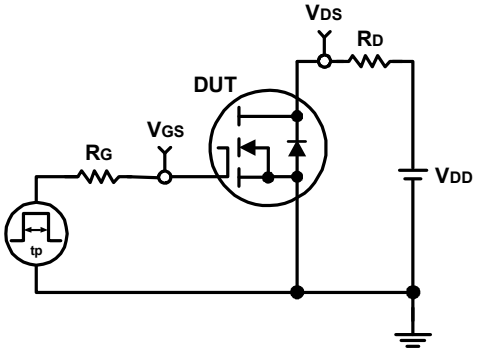


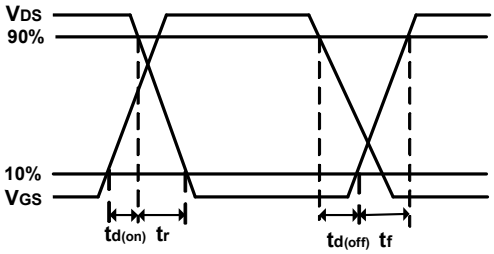
Avalanche Test Circuit and Waveforms





Switching Time Test Circuit and Waveforms





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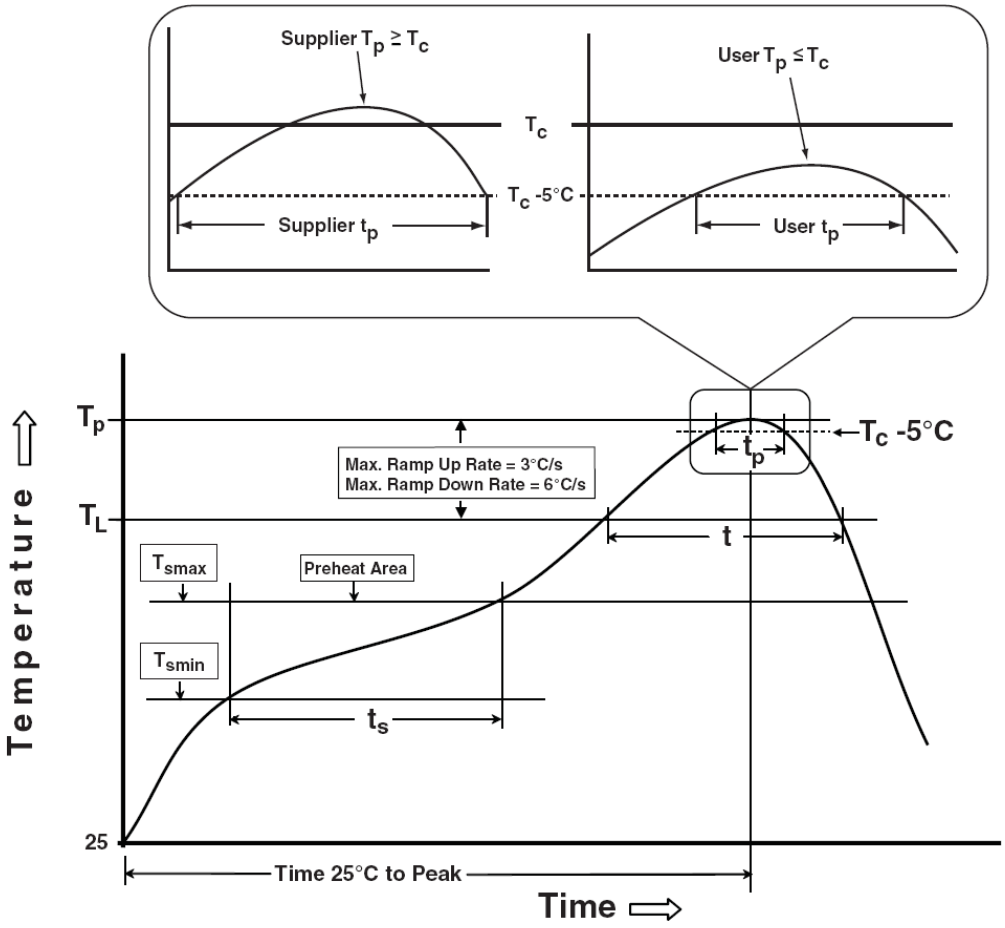
Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak Temperature min (T_{smin}) Temperature max (T_{smax}) Time (T_{smin} to T_{smax}) (t_s)	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-120 seconds
Average ramp-up rate (T_{smax} to T_P)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L) Time at liquidous (t_L)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_P)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm^3 <350	Volume mm^3 ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm^3 <350	Volume mm^3 350-2000	Volume mm^3 >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ Tjmax
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ Tjmax
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

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